IN THE CLAIMS

Please amend the claims as follows.

For the Examiner's convenience, a list of all claims is included below.

1-44 (Cancelled)

45. (Currently Amended) An apparatus for delivering media to a wafer, comprising:

a housing defining a process chamber; and

~~a media delivery member coupled to the process chamber;~~

a spin chuck positioned in the process chamber, the spin chuck having a wafer support surface, the wafer support surface coated with a coating layer such that at least a portion of a particulate matter on the wafer support surface is encapsulated by the coating layer. ~~wherein the wafer support surface is formed with silicon oxide coated contact points; and~~

~~a vacuum supply line coupled to the spin chuck~~.

46. (Currently Amended) The apparatus of claim 45, wherein the coating layer is comprised of a dielectric coating ~~layer~~ material.

47. (Previously presented) The apparatus of claim 45, wherein the coating layer has a composition including a substance from the chemical family SiO_xCH_y, with x ranging from 1-2, inclusive, and y ranging from 0-3, inclusive.

48. (Cancelled)

49. (Cancelled)

50. (Previously presented) The apparatus of claim 45, wherein the coating layer material has a mechanical hardness equal to $hardness_{coatinglayer}$, and silicon has a mechanical hardness equal to $hardness_{silicon}$, and wherein $hardness_{coatinglayer}$ is less than $hardness_{silicon}$.

51. (Previously presented) The apparatus of claim 45, wherein the coating layer has a thickness in the range of 10-100 micrometers.

52. (Previously presented) The apparatus of claim 45, wherein the coating layer has a thickness in the range of 1-10 micrometers.

53. (Previously presented) The apparatus of claim 45, wherein the coating layer has a thickness in the range of 0.05-1 micrometers.

54. (Currently Amended) The apparatus of claim 45, wherein the coating layer has a thickness in the range ~~material on the wafer support surface has a thickness~~ of 10-100 ~~microns~~ micrometers.

55 – 59. (Cancelled)

60. (Currently Amended) An apparatus of claim 45, further comprising a skirt positioned at a periphery and in a non-planar relationship to the wafer support ~~wafer~~ surface.

61. (Previously presented) The apparatus of claim 60, wherein the wafer support surface provides a mechanical support for a wafer and the skirt is positioned to be in a non-mechanical supporting position relative to the wafer.

62. (Previously presented) The apparatus of claim 60, wherein the skirt is sized to permit a wafer positioned on the wafer support surface to extend beyond a periphery of the skirt.

63. (Previously presented) The apparatus of claim 60, wherein the skirt and wafer support surface are sized to be at least equal to a size of a wafer positioned on the wafer support surface.

64. (Cancelled)

65. (New) The apparatus of claim 45 wherein the wafer support surface has formed thereon a plurality of wafer contact points.

66. (New) The apparatus of claim 45 wherein the coating layer promotes a cross-linking of a material comprising the wafer support surface.

67. (New) The apparatus of claim 50 wherein the mechanical hardness of the coating layer is sufficient to reduce a transfer of material from the wafer support surface to wafer.

68. (New) A method comprising:

selecting a coating material for a wafer support surface of a spin chuck; and

coating the wafer support surface of the spin chuck with the coating material such that at least a portion of a particulate matter upon the wafer support surface is encapsulated.

69. (New) The method of claim 68 wherein the coating material is selected based upon a composition of a wafer.